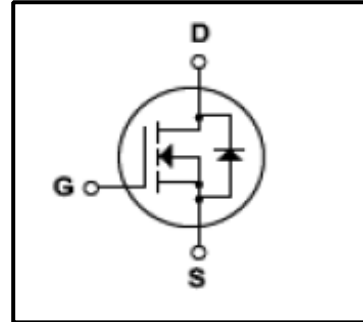


**Silicon N-Channel MOSFET**

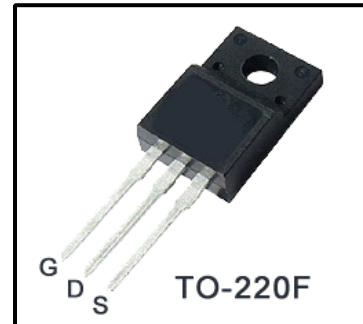
**Features**

- 4.5A,800V, $R_{DS(on)}$ (Max2.5 $\Omega$ )@ $V_{GS}=10V$
- Ultra-low Gate charge(Typical 14nC)
- Fast Switching Capability
- 100%Avalanche Tested
- Maximum Junction Temperature Range(150 $^{\circ}C$ )



**General Description**

This Power MOSFET is produced using Winsemi's advanced planar stripe,VDMOS technology.this latest technology has been especially designed to minimize on-state resistance, have a high rugged avalanche characteristics .This devices is specially well suited for half bridge and full bridge resonant topology line a electronic lamp ballast, high efficiency switched mode power supplies, active power factor correction.



**Absolute Maximum Ratings**

Symbol	Parameter	Value	Units
$V_{DSS}$	Drain Source Voltage	800	V
$I_D$	Continuous Drain Current(@ $T_c=25^{\circ}C$ )	4.5*	A
	Continuous Drain Current(@ $T_c=100^{\circ}C$ )	2.5*	A
$I_{DM}$	Drain Current Pulsed (Note1)	16*	A
$V_{GS}$	Gate to Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note2)	230	mJ
$I_{AR}$	Avalanche Current (Note1)	4	
$E_{AR}$	Repetitive Avalanche Energy (Note1)	11	mJ
dv/dt	Peak Diode Recovery dv /dt (Note3)	4.5	V/ns
$P_D$	Total Power Dissipation(@ $T_c=25^{\circ}C$ )	33	W
	Derating Factor above 25 $^{\circ}C$	0.43	W/ $^{\circ}C$
$T_J$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature	-55~150	
$T_L$	Channel Temperature	300	$^{\circ}C$

\*Drain current limited by maximum junction temperature

**Thermal Characteristics**

Symbol	Parameter	Value			Units
		Min	Typ	Max	
$R_{QJC}$	Thermal Resistance , Junction -to -Case	-	-	3.79	$^{\circ}C/W$
$R_{QJA}$	Thermal Resistance , Junction-to-Ambient	-	-	62.5	$^{\circ}C/W$

## Electrical Characteristics(Tc=25°C)

Characteristics		Symbol	Test Condition	Min	Type	Max	Unit
Gate leakage current		I <sub>GSS</sub>	V <sub>GS</sub> =±30V,V <sub>DS</sub> =0V	-	-	±100	nA
Gate-source breakdown voltage		V <sub>(BR)GSS</sub>	I <sub>G</sub> =±10 μA,V <sub>DS</sub> =0V	±30	-	-	V
Drain Cut -off current		I <sub>DSS</sub>	V <sub>DS</sub> =800V,V <sub>GS</sub> =0V,Tc=25°C	-	-	10	μA
			V <sub>DS</sub> =640V,Tc=125°C	-	-	100	μA
Drain -source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> =250 μA,V <sub>GS</sub> =0V	800	-	-	V
Breakdown Voltage Temperature		ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	I <sub>D</sub> =250μA,referenced to25°C	-	0.65	-	V/°C
Gate threshold voltage		V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250 μA	2	-	4	V
Drain -source ON resistance		R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V,I <sub>D</sub> =2.25A	-	2.0	2.5	Ω
Forward Transconductance		g <sub>fs</sub>	V <sub>DS</sub> =40V,I <sub>D</sub> =2.25A	-	4.6	-	S
Input capacitance		C <sub>iss</sub>	V <sub>DS</sub> =25V,	-	1320	1716	pF
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>GS</sub> =0V,	-	9	12	
Output capacitance		C <sub>oss</sub>	f=1MHz	-	105	136	
Switching time	Turn-on Rise time	t <sub>r</sub>	V <sub>DD</sub> =400V,	-	85	155	ns
	Turn-on delay time	T <sub>d(on)</sub>	I <sub>D</sub> =4.5A	-	34	75	
	Turn-off Fall time	t <sub>f</sub>	R <sub>G</sub> =25Ω	-	59	118	
	Turn-off delay time	T <sub>d(off)</sub>	(Note4,5)	-	56	113	
Total gate charge(gate-source plus gate-drain)		Q <sub>g</sub>	V <sub>DD</sub> =640V, V <sub>GS</sub> =10V,	-	14	19	nC
Gate-source charge		Q <sub>gs</sub>	I <sub>D</sub> =4.5A	-	5	-	
Gate-drain("miller") Charge		Q <sub>gd</sub>	(Note,5)	-	6	-	

## Source-Drain Ratings and Characteristics(Ta=25°C)

Characteristics	Symbol	Test Condition	Min	Type	Max	Unit
Continuous drain reverse current	I <sub>DR</sub>	-	-	-	4.5	A
Pulse drain reverse current	I <sub>DRP</sub>	-	-	-	16	A
Forward voltage(diode)	V <sub>DSF</sub>	I <sub>DR</sub> =4.5A,V <sub>GS</sub> =0V	-	-	1.4	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> =4.5A,V <sub>GS</sub> =0V,	-	625	-	ns
Reverse recovery charge	Q <sub>rr</sub>	dI <sub>DR</sub> /dt =100 A /μs	-	6.71	-	μC

Note 1.Repeativity rating :pulse width limited by junction temperature

2.L=40mH I<sub>AS</sub>=4.5A,V<sub>DD</sub>=50V,R<sub>G</sub>=25Ω,Starting T<sub>J</sub>=25°C

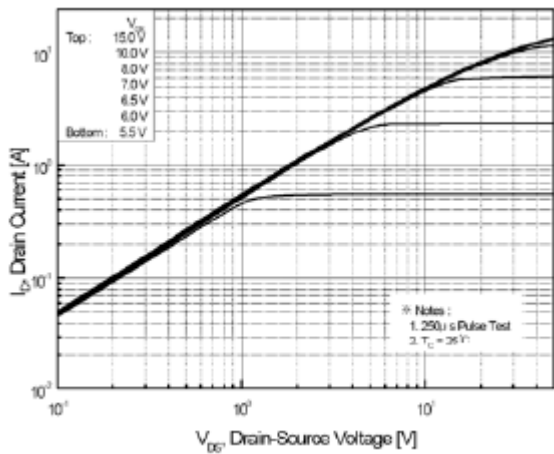
3.I<sub>SD</sub>≤4.5A,di/dt≤200A/μs,V<sub>DD</sub><BV<sub>DSS</sub>,STARTING T<sub>J</sub>=25°C

4.Pulse Test:Pulse Width≤300us,Duty Cycle≤2%

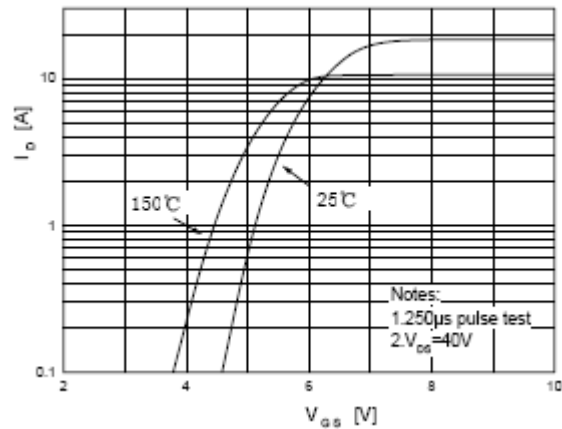
5. Essentially independent of operating temperature.

This transistor is an electrostatic sensitive device

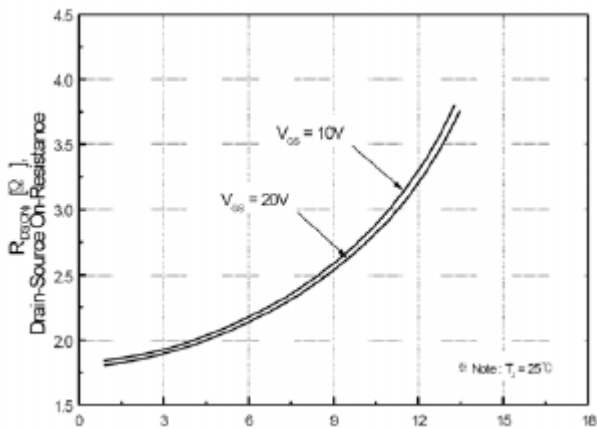
Please handle with caution



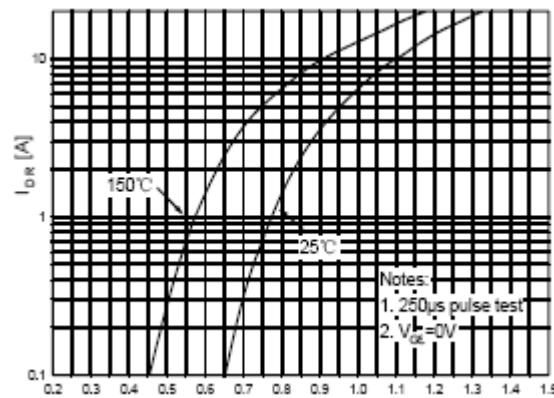
**Fig.1 On-State characteristics**



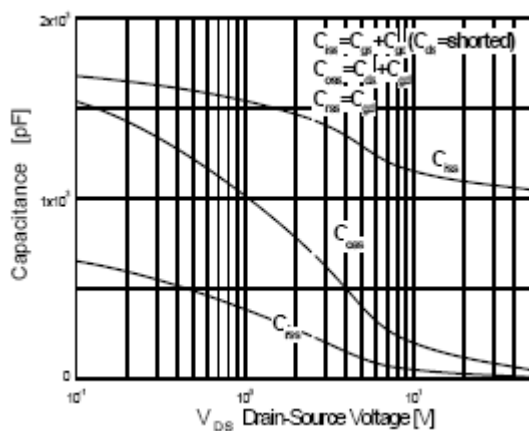
**Fig.2 Transfer characteristics**



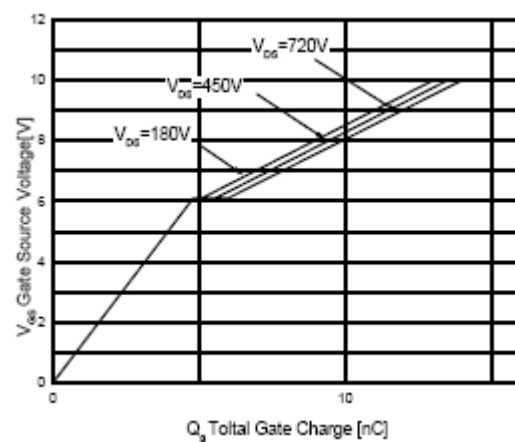
**Fig.3 On-Resistance Variation vs Drain Current and Gate Voltage**



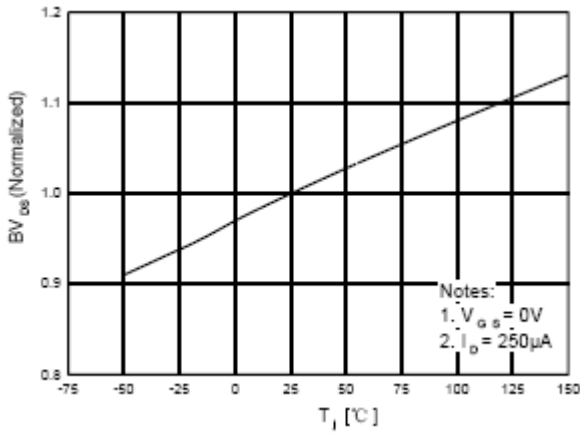
**Fig.4 Body Diode Forward Voltage Variation with Source Current and Temperature**



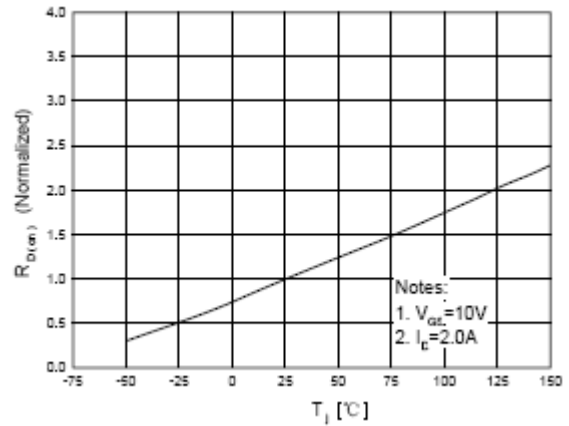
**Fig.5 Capacitance Characteristics**



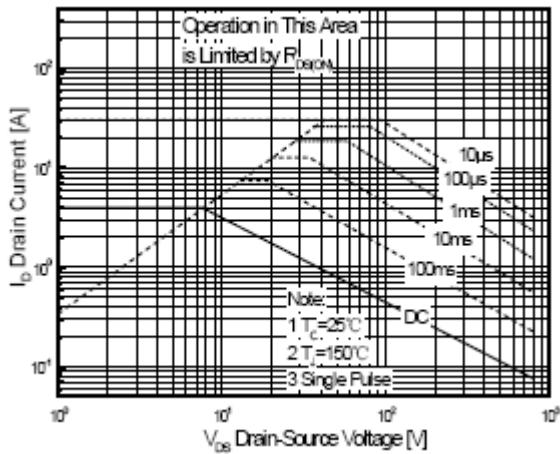
**Fig.6 Gate Charge Characteristics**



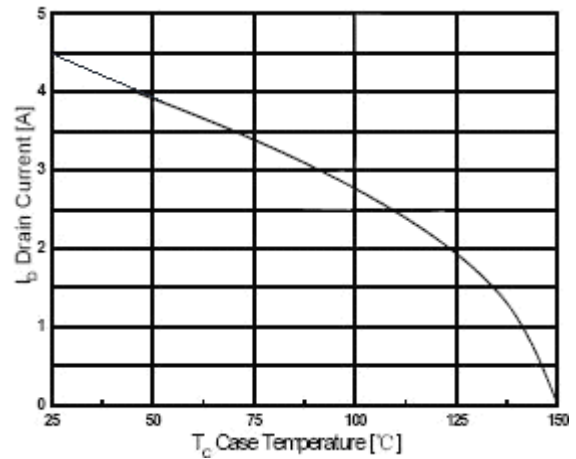
**Fig.7 Breakdown Voltage Variation vs. Temperature**



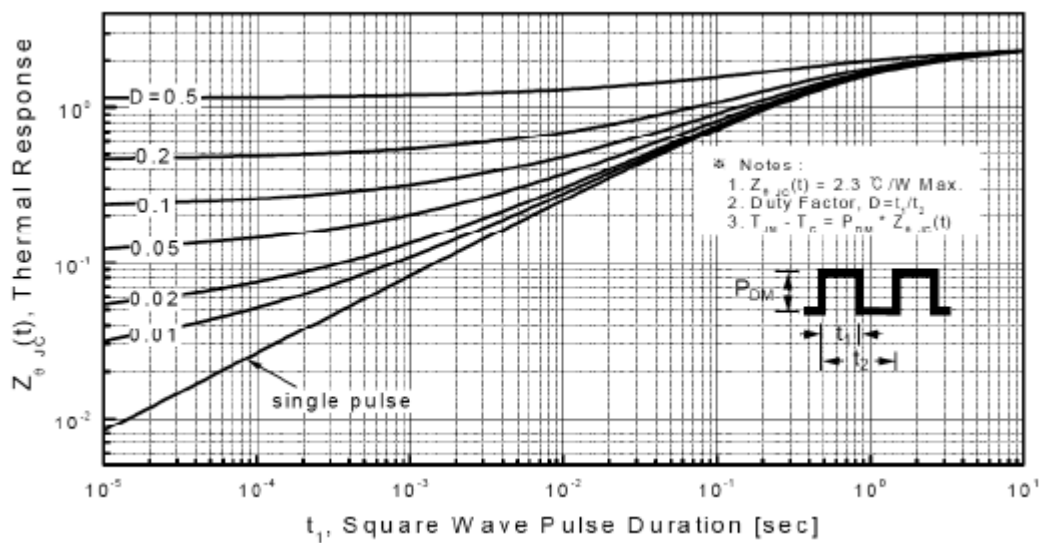
**Fig.8 On-Resistance Variation vs. Temperature**



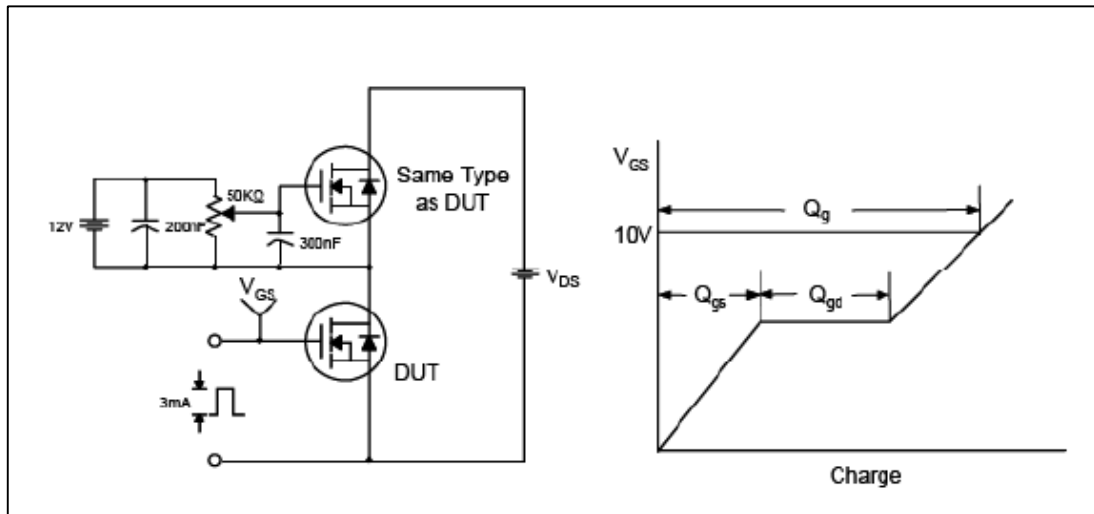
**Fig.9 Maximum Safe Operation Area**



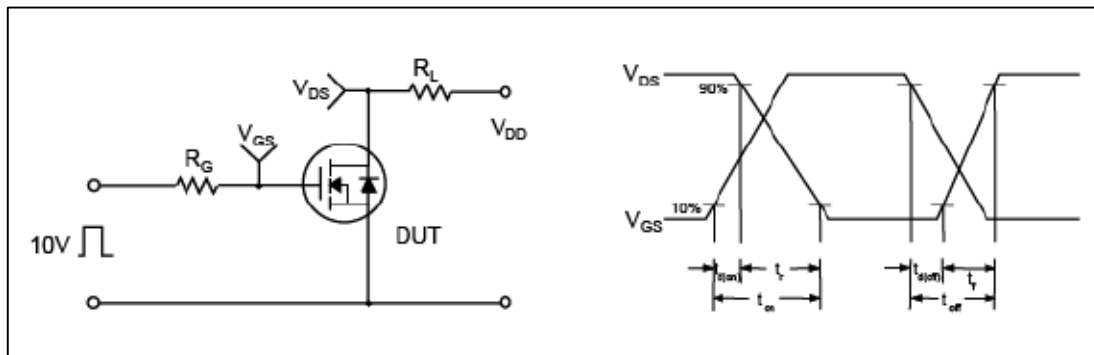
**Fig.10 Maximum Drain Current vs Case Temperature**



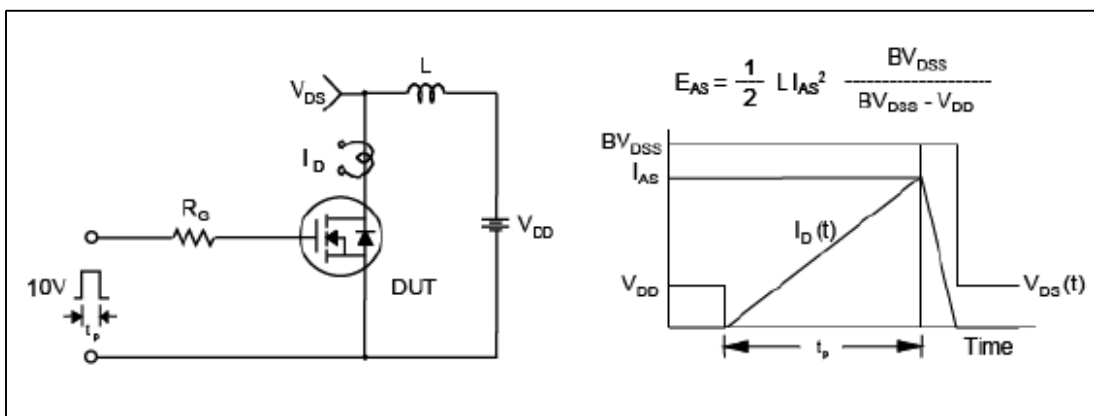
**Fig.11 Transient Thermal Response Curve**



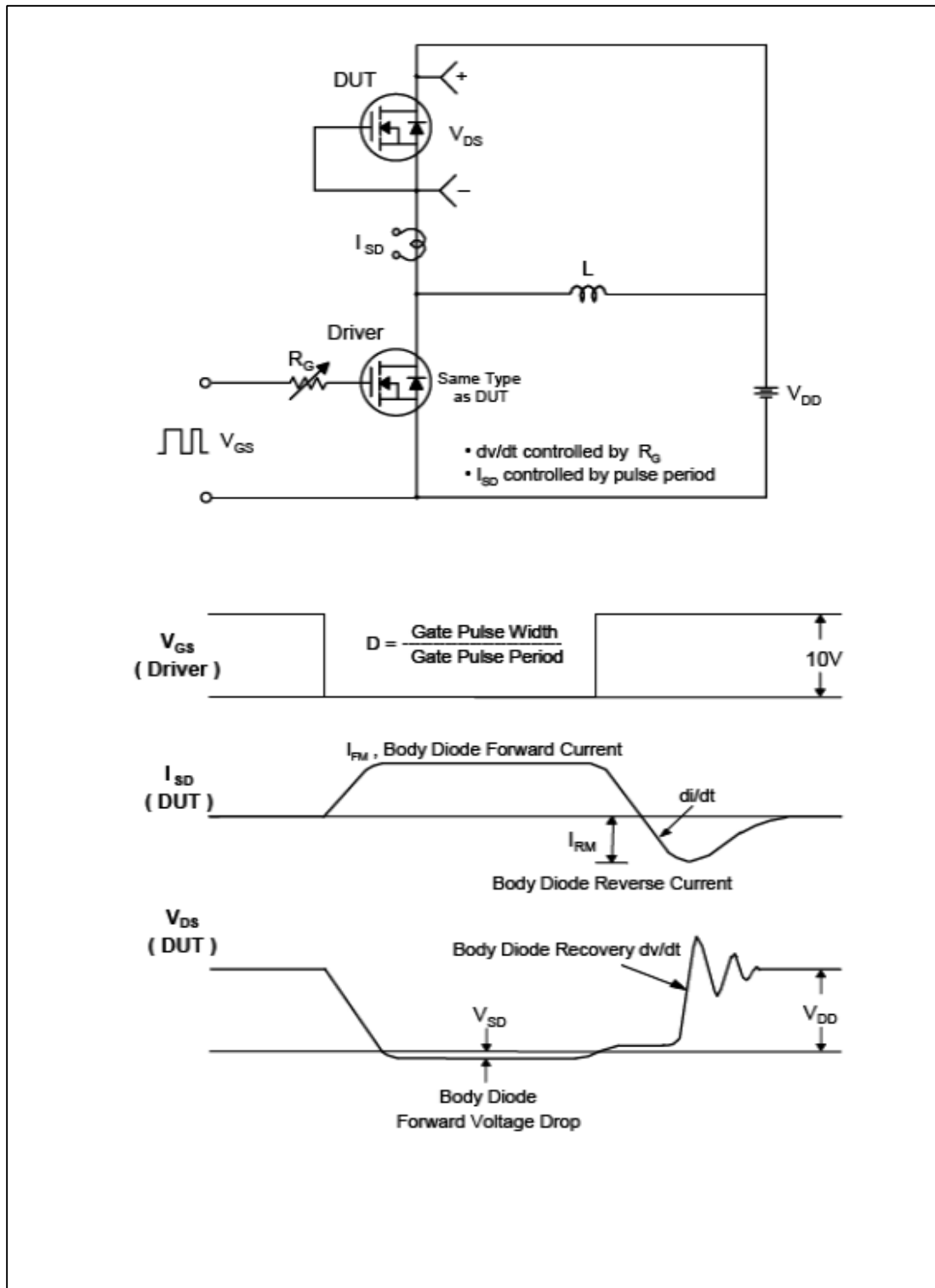
**Fig.12 Gate Test Circuit & Waveform**



**Fig.13 Resistive Switching Test Circuit & Waveform**



**Fig.14 Unclamped Inductive Switching Test Circuit & Waveform**



**Fig.15 Peak Diode Recovery dv/dt Test Circuit & Waveform**

**TO-220F Package Dimension**

